

IN THE SPECIFICATION:

Please replace the paragraph at page 27, lns. 9-22 as follows:

The n-channel TFT 501 of the driver circuit 506 includes the channel forming region 423c (Fig. 3C), the lightly-doped impurity regions 423b ([GOLD] LDD regions) which are overlapped by a first conductive layer 428a (Fig. 3C) forming part of the gate electrode, and the heavily-doped impurity regions 423a which function as the source region and drain region. The p-channel TFT 502 which forms the CMOS circuit by being connected with the n-channel TFT 501 through the electrode 466, includes the channel forming region 446d (Fig. 4C), the impurity regions 446b and 446c which are formed outside the gate electrode, and the heavily-doped impurity regions 446a which function as the source region and drain region. Besides, the n-channel TFT 503 includes the channel forming region 425c (Fig. 3C), the lightly-doped impurity regions 425b ([GOLD] LDD regions) which are overlapped by a first conductive layer 430a (Fig. 3C) forming part of the gate electrode, and the heavily-doped impurity regions 425a which function as the source region and drain region.

Please replace the paragraph at page 29, lns. 1-9 as follows:

In this embodiment, the substrate shown in Embodiment 2 is used. Accordingly, in Fig. 7 showing a top view of the pixel portion in accordance with Embodiment 2, light shielding must be performed in at least gaps between the gate wiring 469 and the pixel electrodes 473, a gap between the gate wiring 469 and the connection electrode 468, and a gap between the connection electrode 468 and the pixel electrode 473. In this embodiment, the opposing substrate and the active matrix substrate are stuck so that the light shielding portions from laminated layer of colored layer each other overlap with the positions which need to be shielded from light.